





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	I _D Τ _A = 25°C
	0.4Ω @ $V_{GS} = 4.5V$	1.5A
20V	0.5Ω @ $V_{GS} = 2.5V$	1.3A
	0.7Ω @ $V_{GS} = 1.8V$	1.1A

Features and Benefits

- Low On-Resistance
- Very Low Gate Threshold Voltage V_{GS(TH)}, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surfaced Mount Package
- Ultra-low package profile, 0.4mm maximum package height
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power management functions

Mechanical Data

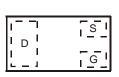
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 @
- Weight: 0.001 grams (approximate)



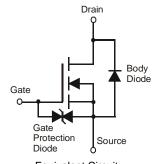


X2-DFN1006-3

Bottom View



Top View Internal Schematic



Equivalent Circuit

Ordering Information (Note 4)

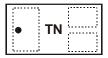
Part Number	Case	Packaging
DMN2501UFB4-7	X2-DFN1006-3	3,000/Tape & Reel
DMN2501UFB4-7B	X2-DFN1006-3	10.000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

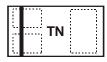
Marking Information

DMN2501UFB4-7



Top View Dot Denotes Drain Side

DMN2501UFB4-7B



Top View Bar Denotes Gate and Source Side

TN = Product Type Marking Code



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	20	V		
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Desir Courset (Note 5) V	Steady State	T _A = 25°C T _A = 70°C	ID	1.0 0.8	А
Continuous Drain Current (Note 5) V _{GS} = 4.5V	t<10s	T _A = 25°C T _A = 70°C	I _D	1.2 0.9	А
Continuous Desir Courset (Nata C) V	Steady State	T _A = 25°C T _A = 70°C	I _D	1.5 1.2	А
Continuous Drain Current (Note 6) V _{GS} = 4.5V	t<10s	T _A = 25°C T _A = 70°C	I _D	1.8 1.4	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	6	Α
Maximum Body Diode continuous Current			I _S	1	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

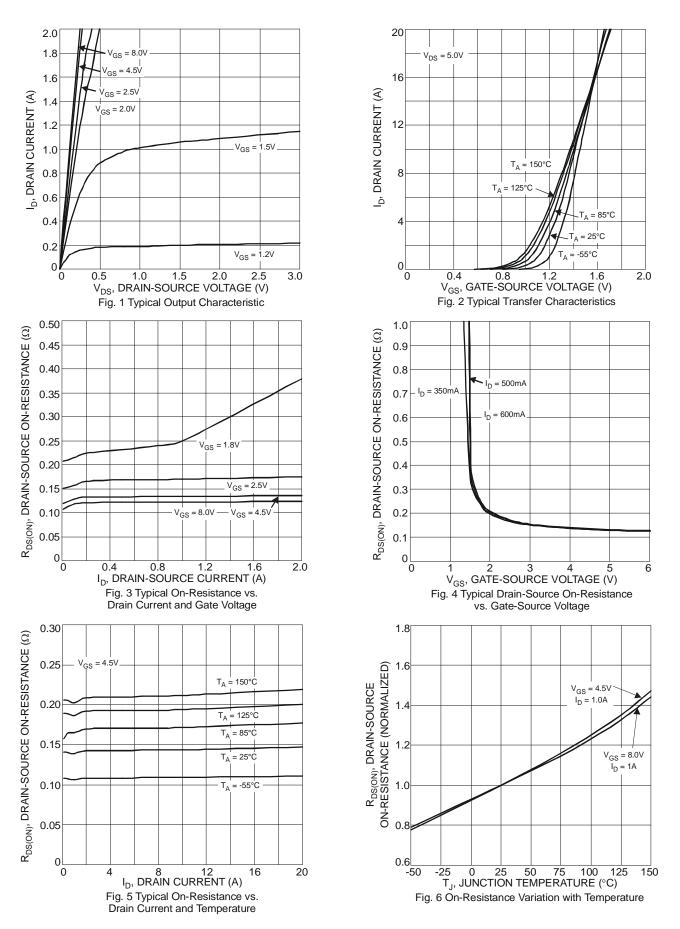
Characteristic	Symbol	Value	Units	
Total Bower Dissipation (Note 5)	$T_A = 25^{\circ}C$	D-	0.5	W
Total Power Dissipation (Note 5)	$T_A = 70^{\circ}C$	P _D	0.3	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	6	251	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	188	
Total Power Dissipation (Note 6)	$T_A = 25^{\circ}C$	C	1.2	W
Total Power Dissipation (Note 6)	$T_A = 70^{\circ}C$	P_{D}	0.7	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	C	110	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	82	
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

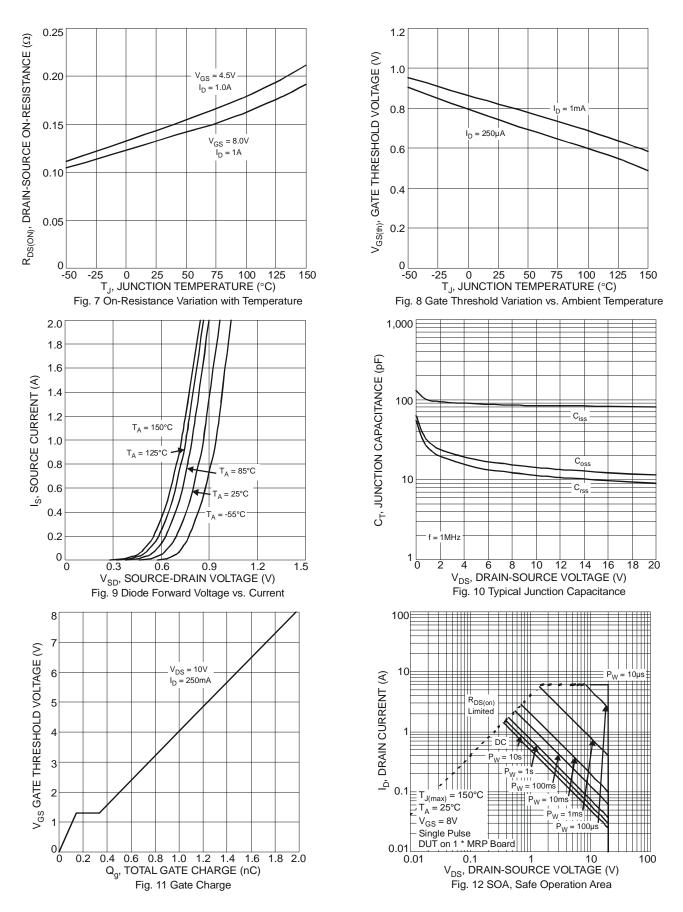
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	100	nA	$V_{DS} = 20V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±1	μΑ	$V_{GS} = \pm 6V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	0.5	0.76	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
			170	400		$V_{GS} = 4.5V, I_D = 600mA$	
Static Drain-Source On-Resistance	R _{DS} (ON)	-	200	500	$m\Omega$	$V_{GS} = 2.5V, I_D = 500mA$	
			260	700		$V_{GS} = 1.8V, I_D = 350mA$	
Forward Transfer Admittance	Y _{fs}	-	1.4	-	S	$V_{DS} = 10V, I_{D} = 400mA$	
Diode Forward Voltage	V _{SD}		0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	82	-	pF	101/1/	
Output Capacitance	Coss	-	12	-	рF	$V_{DS} = 16V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	-	10	-	pF	1 = 1.0lvii iz	
Gate resistance	Rg	-	83	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	1.1	-	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	-	2.0	-	nC	\/ 40\/ I 250m A	
Gate-Source Charge	Q _{gs}	-	0.14	-	nC	$V_{DS} = 10V, I_D = 250mA$	
Gate-Drain Charge	Q _{gd}	-	0.19	-	nC		
Turn-On Delay Time	t _{D(on)}	-	6.6	-	ns		
Turn-On Rise Time	t _r	-	6.4	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(off)}	-	40.4	-	ns	$R_L = 47\Omega$, $R_G = 10\Omega$,	
Turn-Off Fall Time	t _f	-	17.3	-	ns	$I_D = 200 \text{mA}$	

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:

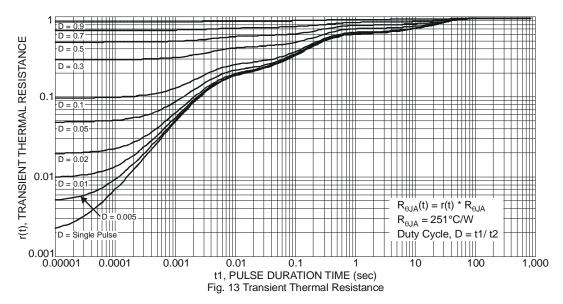






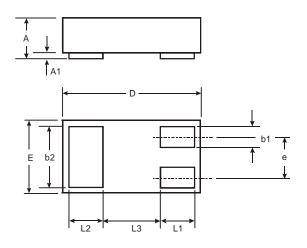






Package Outline Dimensions

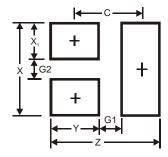
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



X2-DFN1006-3					
Dim	Min	Max	Тур		
Α		0.40			
A1	0	0.05	0.03		
b1	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.05	1.00		
Е	0.55	0.65	0.60		
е	e — 0.35				
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3			0.40		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
Z	1.1			
G1	0.3			
G2	0.2			
Х	0.7			
X1	0.25			
Y	0.4			
С	0.7			



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